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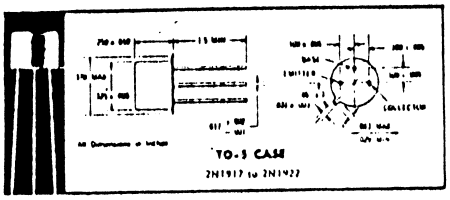
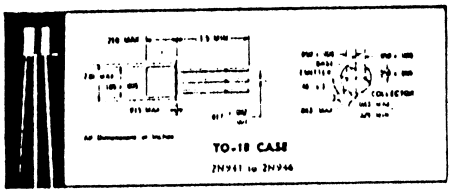
SWITCHING
SILICON EPITAXIAL JUNCTION
PNP TRANSISTORS

2N941 — 2N1917
2N942 — 2N1918
2N943 — 2N1919
2N944 — 2N1920
2N945 — 2N1921
2N946 — 2N1922

- LOW AND HIGH LEVEL CHOPPING
- LOW JUNCTION CAPACITANCE





ELECTRICAL DATA ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	2N941/942 2N1917/1918	2N943/944 2N1919/1920	2N945 2N1921	2N946 2N1922	UNITS
Collector to Emitter Voltage	BV_{CEO}	-8	-18	-50	-80	V
Collector to Base Voltage	BV_{CBO}	-25	-40	-50	-80	V
Emitter to Base Voltage	BV_{EBO}	-25	-40	-50	-80	V
Collector Current	I_C	50mA				
Power Dissipation (free air)	P_D	250mW				
Junction Temp. (Oper. & Store)	T_J	-65°C to +175°C				
Lead Temp. (1/16" ±1/32" From Case)	T_L	240°C for 10 sec.				
Derating Factor (free air)	D_F	1.6mW/°C				

ELECTRICAL CHARACTERISTICS: T_A = 25°C (UNLESS OTHERWISE STATED)

PARAMETER	SYMBOL	Case: TO-18 Case: TO-5 CONDITION	2N941 2N1917 MIN.	2N941 2N1917 MAX.	2N942 2N1918 MIN.	2N942 2N1918 MAX.	2N943 2N1919 MIN.	2N943 2N1919 MAX.	2N944 2N1920 MIN.	2N944 2N1920 MAX.	2N945 2N1921 MIN.	2N945 2N1921 MAX.	2N946 2N1922 MIN.	2N946 2N1922 MAX.	UNITS
Collector-Base Leakage Current	I_{CBO}	V_{CB} = -4.5V, I_E = 0	-	2.5	-	2.5	-	-	-	-	-	-	-	-	nA
Collector-Base Leakage Current	I_{CBO}	V_{CB} = -4.5V, I_E = 0, Temp: +65°C	-	50	-	50	-	-	-	-	-	-	-	-	nA
Emitter-Base Leakage Current	I_{EBO}	V_{EB} = -4.5V, I_C = 0	-	2.5	-	2.5	-	-	-	-	-	-	-	-	nA
Emitter-Collector Inverse Leakage Current	I_{ECX}	V_{EB} = -10V, V_{SC} = -15V	-	-	-	-	-	1.5	-	2.5	-	10.0	-	10.0	nA
Emitter Offset Current	I_{EO}	V_{CB} = -1.5V	-	1.0	-	3.0	-	1.0	-	1.5	-	2.0	-	2.0	nA
Emitter Offset Voltage	V_{EO}	I_B = -250µA, I_C = 0	-	1.0	-	3.0	-	2.0	-	3.0	-	4.0	-	4.0	mV
Collector Saturation Voltage	$V_{CE(sat)}$	I_B = -500µA, I_C = -20µA	-	-	-	-	-	3.0	-	4.0	-	5.0	-	5.0	mV
A.C. Current Gain	h_{fe}	V_{CB} = -6V, I_E = 1.0mA, f = 1KC	25	-	25	-		-		-		-		-	-
High Frequency Current Gain	h_{fe}	V_{CB} = -6V, I_E = 1.0mA, f = 1MC	16	-	16	-	1.0	-	1.0	-	1.0	-	1.0	-	-
Collector to Base Capacitance	C_{ob}	V_{CB} = -6V, I_E = -1.0mA, f = 1MC	-	14	-	14	-	14	-	14	-	14	-	14	pfd

Quality Semi-Conductors